



JCT825CH 25A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT825CH SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially



Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$	-	-	20	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM} T_j=150 R_L=3.3k$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	70	mA
I_H	$I_T=500mA$	-	-	60	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$	00	-	-	V/ μs
	$V_D=540V$ Gate Open $T_j=150$	500	-	-	
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$	-	2	-	μs
t_{off}		-	50	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=50A t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=150$	0.7	V
R_D	Dynamic resistance	$T_j=150$	18	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	0.3	/W
$R_{th(j-a)}$	junction to ambient (DC)	60	/W

JCT825CH

FIG.1: Maximum power dissipation versus RMS on-state current

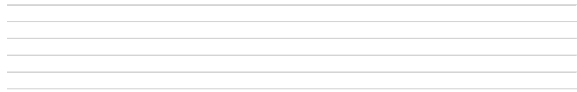


FIG.2: RMS on-state current versus case temperature

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT825CH	800	20	TO-220C	50	Tube


Document Revision History

Date	Revision	Changes
Jun.15, 2023	A.	

PACKAGE MECHANICAL DATA



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd. Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.